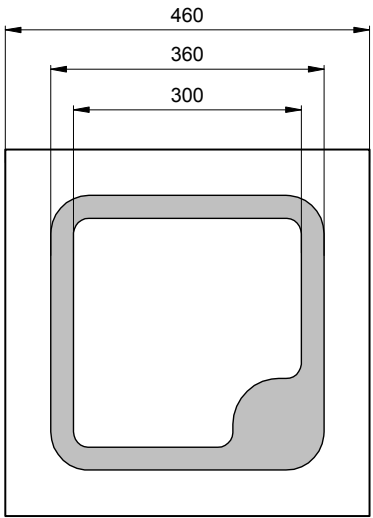


| Radiation | Type | Technology | Electrodes |
|-----------|------|-------------|----------------|
| Infrared | MQW | InGaAs/GaAs | N (cathode) up |

| | | |
|--|--|--|
|  <p style="text-align: center;">PD-02</p> | typ. dimensions (μm) | |
| | <u>typ. thickness</u> 260 (±20) μm <u>cathode</u> gold alloy, 1.5 μm <u>anode</u> gold alloy, 1.5 μm, solderable | |

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

| Parameter | Test conditions | Symbol | Min | Typ | Max | Unit |
|----------------------------|-------------------------|---------------------------------|------|------|------|------|
| Forward voltage | I _F = 100 mA | V _F | | 1.2 | 1.4 | V |
| Reverse voltage | I _R = 10 μA | V _R | 10 | | | V |
| Radiant power ¹ | I _F = 100 mA | Φ _e | 0.75 | 1.5 | | mW |
| Radiant power ² | I _F = 100 mA | Φ _e | | 3.0 | | mW |
| Peak wavelength | I _F = 100 mA | λ _p | 1000 | 1020 | 1050 | nm |
| Spectral bandwidth at 50% | I _F = 100 mA | Δλ _{0.5} | | 80 | | nm |
| Switching time | I _F = 100 mA | t _r , t _f | | 10 | | ns |

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

²Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

Labeling

| Type | Lot N° | Φ _e (typ) [mW] | V _F (typ) [V] | Quantity |
|---------------|--------|---------------------------|--------------------------|----------|
| ELC-1020-28-1 | | | | |

Packing: Chips on adhesive film with wire-bond side on top